

GSM12Z

TVS Diode Array

DESCRIPTION

The GSM12Z of transient voltage suppressors (TVS) are designed to protect components which are connected to data and transmission lines from voltage surges caused by electrostatic discharge (ESD), electrical fast transients (EFT), and lightning.

TVS diodes are characterized by their high surge capability, low operating and clamping voltages, and fast response time. This makes them ideal for use as board level protection of sensitive semiconductor components. The dual-junction common-anode design allows the user to protect one bidirectional data line or two unidirectional lines. The low profile SOT-23 package allows flexibility in the design of "crowded" circuit boards. The GSM12Z will meet the surge requirements of IEC 61000-4-2 (Formerly IEC 801-2), Level 4, "Human Body Model" for air and contact discharge.

ORDERING INFORMATION

- ♦Device: GSM12Z
- ♦Package: SOT-23
- ♦Marking:12C
- ♦ Material: Halogen free
- ♦Packing: Tape & Reel
- ♦Quantity per reel: 3,000pcs

PIN CONFIGURATION



FEATURES

- ♦IEC61000-4-2 (ESD) ±15kV (air), ±8kV (contact)
- IEC61000-4-4 (EFT) 40A (5/50ηs)
- \diamond 550 Watts Peak Pulse Power per (tp=8/20µs)
- Protects one bidirectional line or two unidirectional lines
- ♦Low clamping voltage
- ♦Working voltages : 12V
- ♦Low leakage current

MACHANICAL DATA

- ♦SOT-23 package
- ♦ Flammability Rating: UL 94V-0
- \diamond Packaging: Tape and Reel
- ♦High temperature soldering guaranteed: 260°C/10s
- ♦Reel size: 7 inch
- ∻MSL 1

APPLICATIONS

- ♦ Cellular Handsets and Accessories
- ♦Portable Electronics
- ♦Industrial Controls
- ♦ Set-Top Box
- Servers, Notebook, and Desktop PC

PACKAGE OUTLINE







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ABSOLUTE MAXIMUM RATING							
Symbol	Parameter	Value	Units				
V _{ESD}	ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	±30 ±30	kV				
P _{PP}	Peak Pulse Power (8/20µs)	550	W				
T _{OPT}	Operating Temperature	-55/+150	°C				
T _{STG}	Storage Temperature	-55/+150	°C				
TL	Lead Soldering Temperature	260 (10 sec.)	°C				

ELECTRICAL CHARACTERISTICS (Tamb=25°C)									
Symbol	Parameter	Test Condition	Min	Тур	Мах	Units			
V _{RWM}	Reverse Working Voltage				12	V			
V _{BR}	Reverse Breakdown Voltage	I _T = 1mA	13.3			V			
I _R	Reverse Leakage Current	V _{RWM} = 12V			1.0	μA			
Vc	Clamping Voltage	I _{PP} = 1A, t _p = 8/20μs			19	V			
V _c	Clamping Voltage	I _{PP} = 22Α, t _p = 8/20μs			25	V			
CJ	Junction Capacitance	V _R = 0V, f = 1MHz		110	150	pF			



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ELECTRICAL CHARACTERISTICS CURVE





Pulse Waveform



SOT-23 PACKAGE OUTLINE DIMENSIONS





	М	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
A	0.89	1.00	1.11	0.035	0.040	0.044	
A1	0.01	0.06	0.10	0.001	0.002	0.004	
b	0.37	0.44	0.50	0.015	0.018	0.020	
С	0.09	0.13	0.18	0.003	0.005	0.007	
D	2.80	2.90	3.04	0.110	0.114	0.120	
E	1.20	1.30	1.40	0.047	0.051	0.055	
е	1.78	1.90	2.04	0.070	0.075	0.081	
L	0.35	0.54	0.69	0.014	0.021	0.029	
HE	2.10	2.40	2.64	0.083	0.094	0.104	

